

FIG. 1

FIG. 2

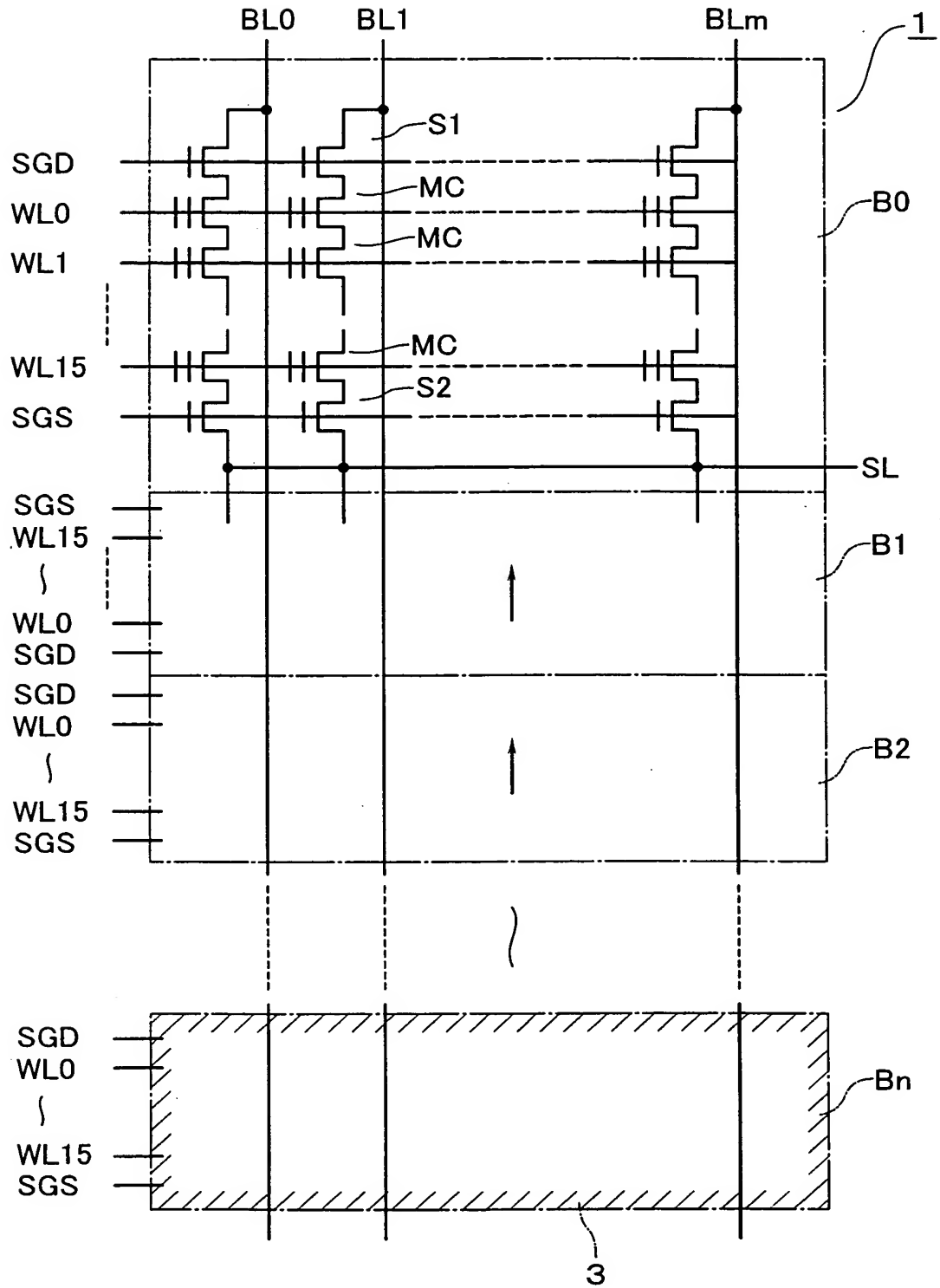


FIG.3A

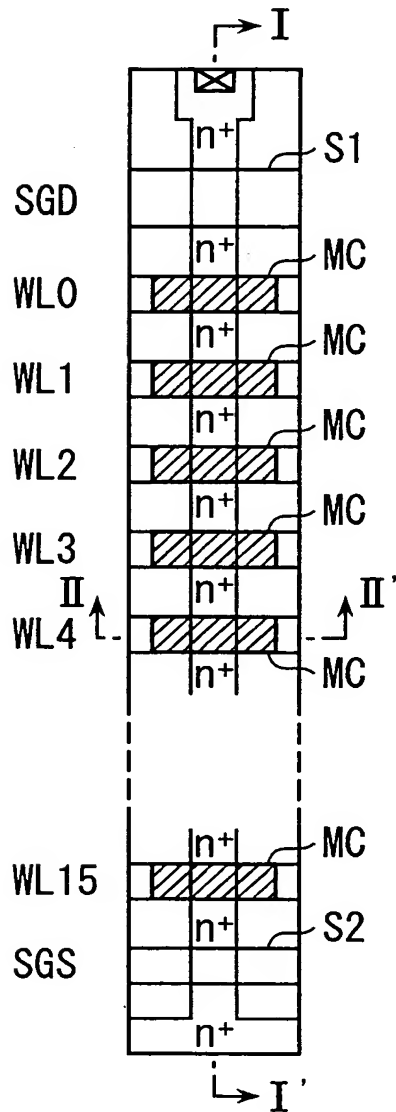
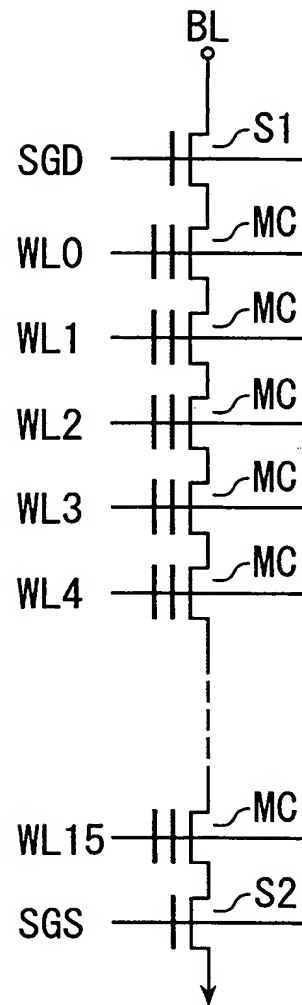


FIG.3B



A cross-sectional view of a semiconductor device. The device consists of a substrate 20 with a p<sup>-</sup> region. A layer 26 is formed on the substrate, containing n<sup>+</sup> regions. A layer 27 is formed on top of layer 26. A layer 28 is formed on top of layer 27. The device is divided into regions labeled (S1), (MC), (MC), (MC), (MC), and (S2). The (S1) and (S2) regions have a different structure than the (MC) regions. The (MC) regions have a structure with layers 24, 22, 24, 22, 24, 22, 28. The (S1) and (S2) regions have a structure with layers 24, 22, 28. The (S1) and (S2) regions are separated by a gap.

FIG.5

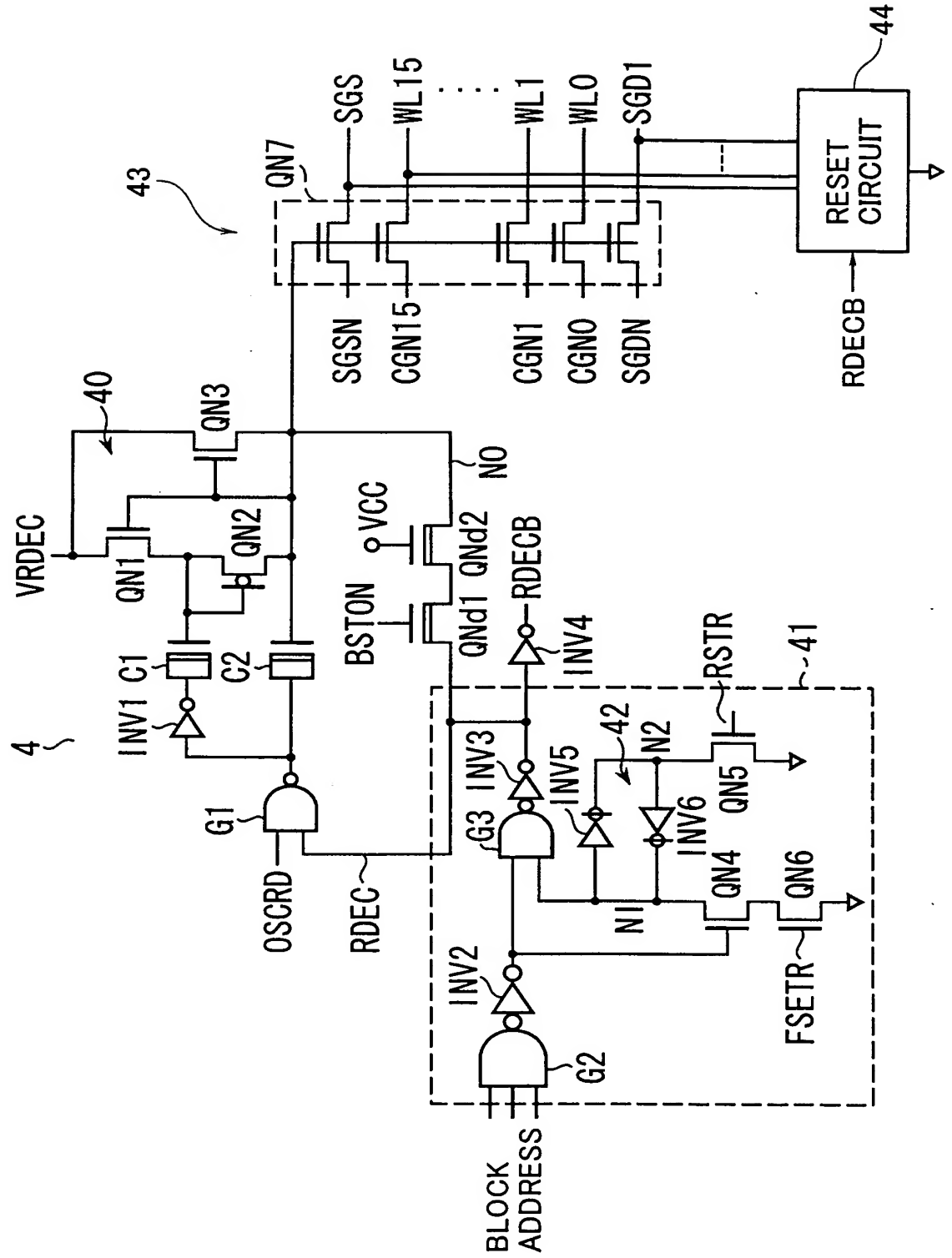
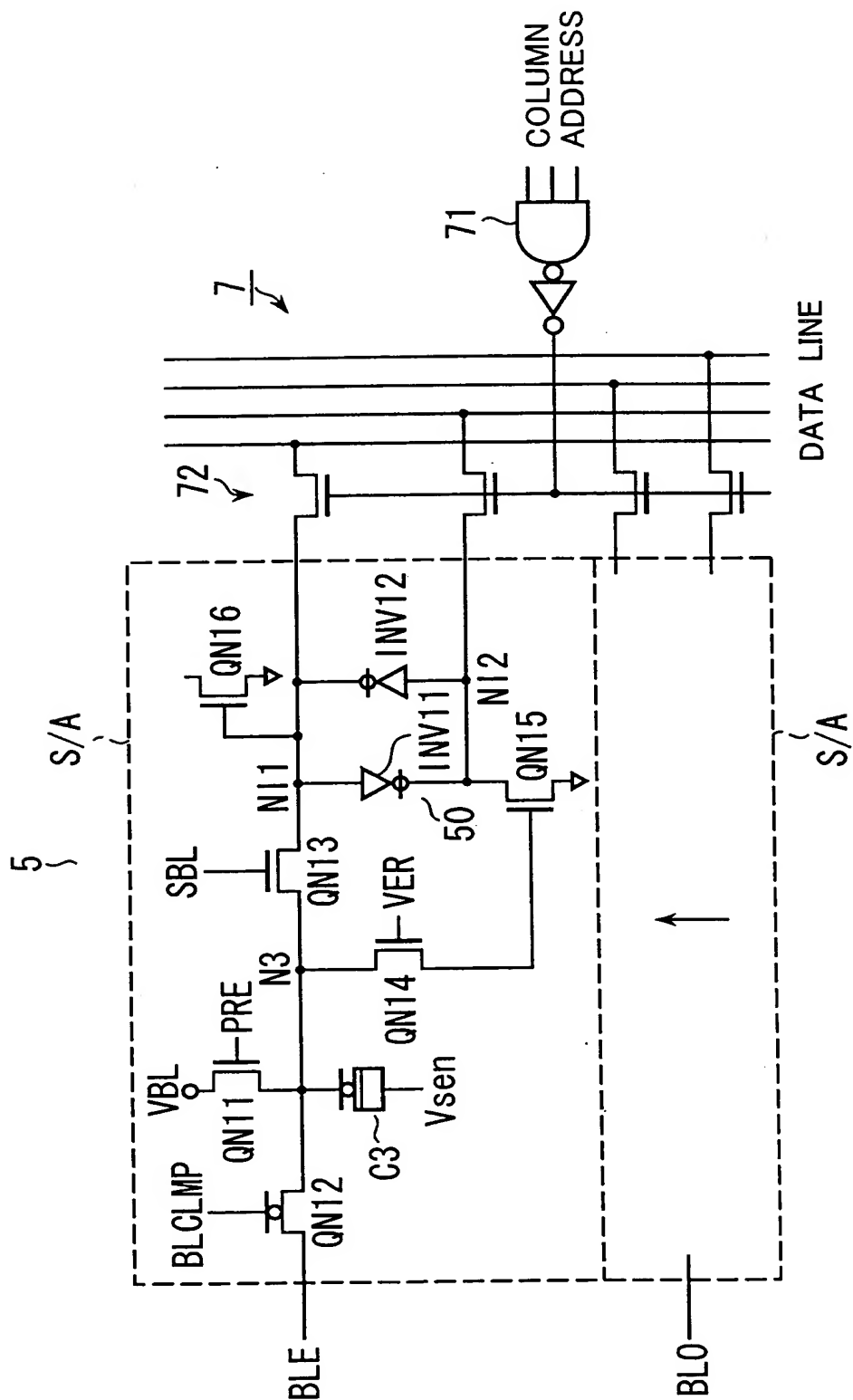


FIG. 6



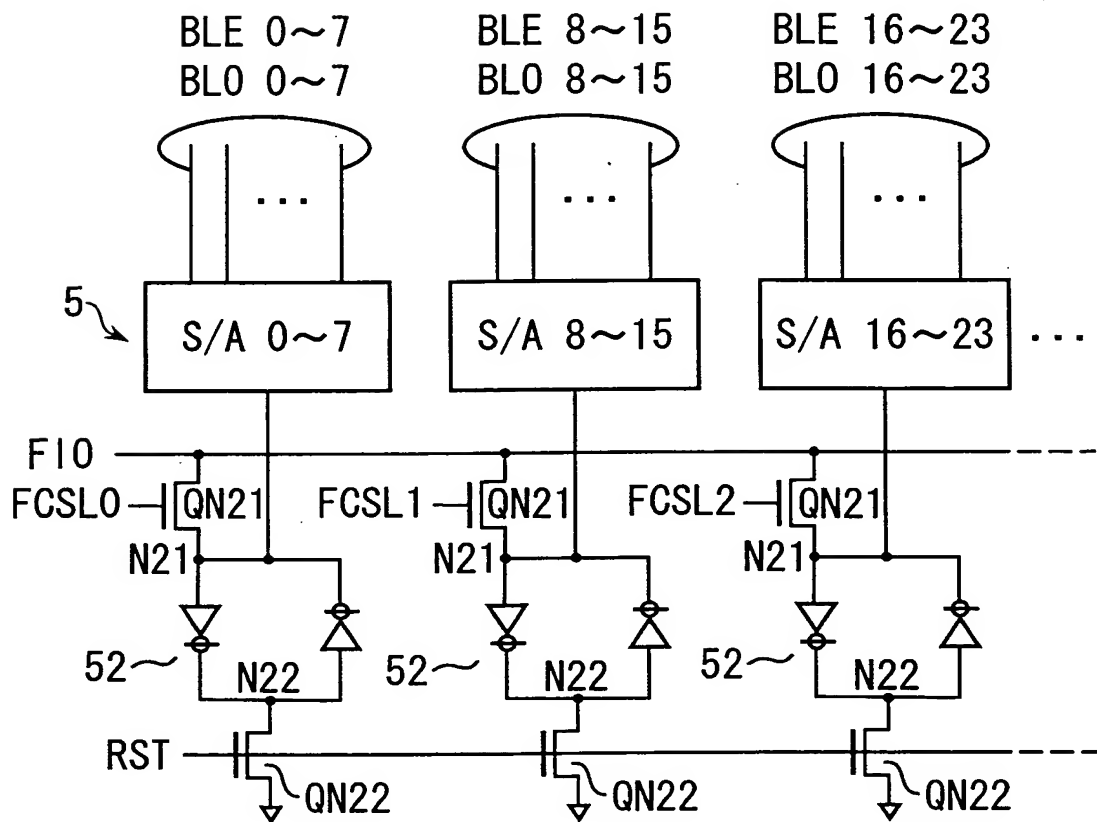


FIG.8

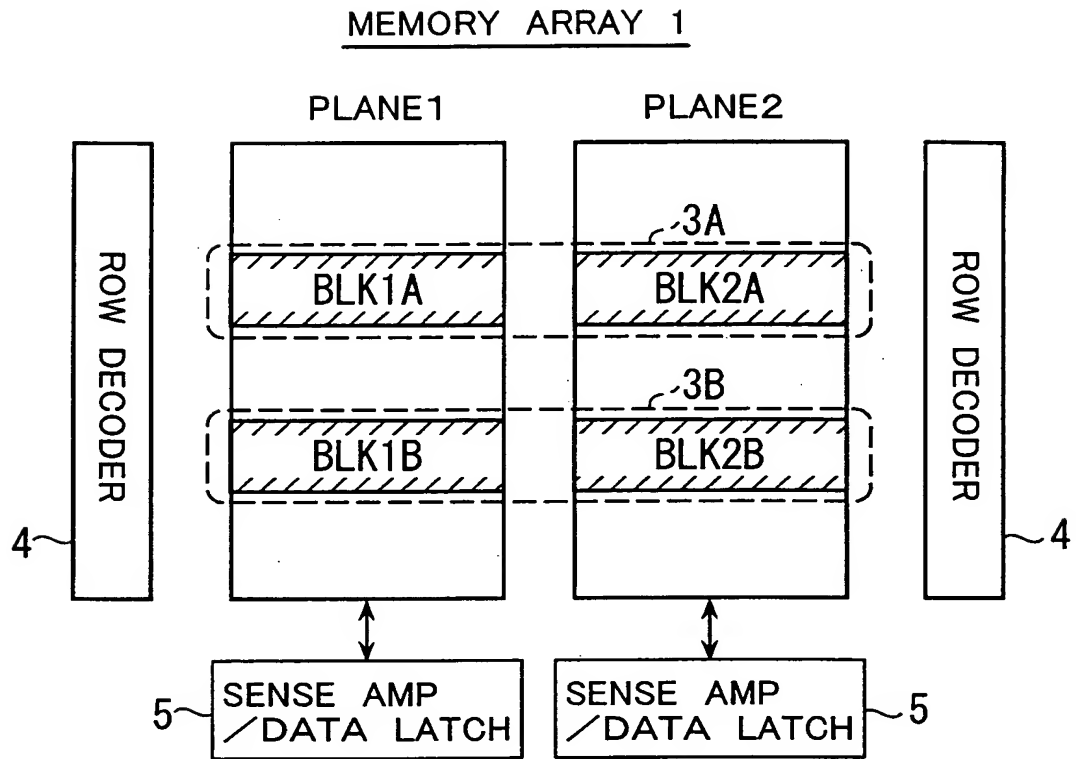


FIG.9

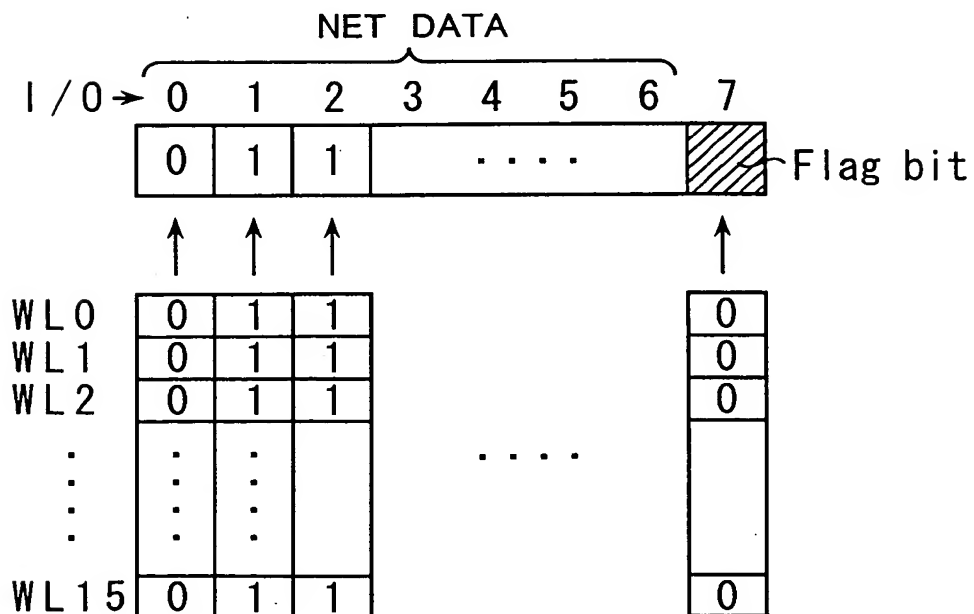


FIG.10A

EVEN PAGE (DEFECTIVE COLUMN ADDRESS)

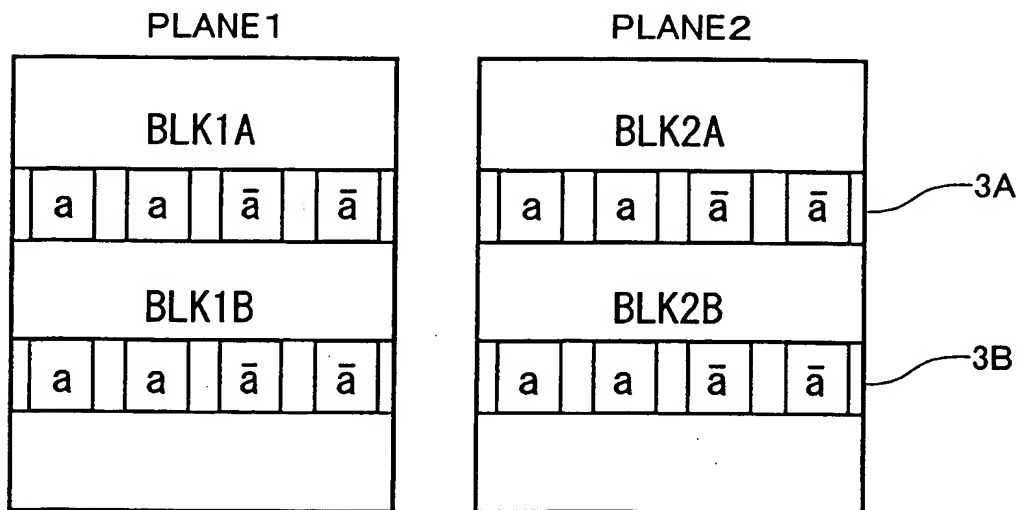


FIG.10B

ODD PAGE (DEFECTIVE BLOCK ADDRESS+OPTION DATA)

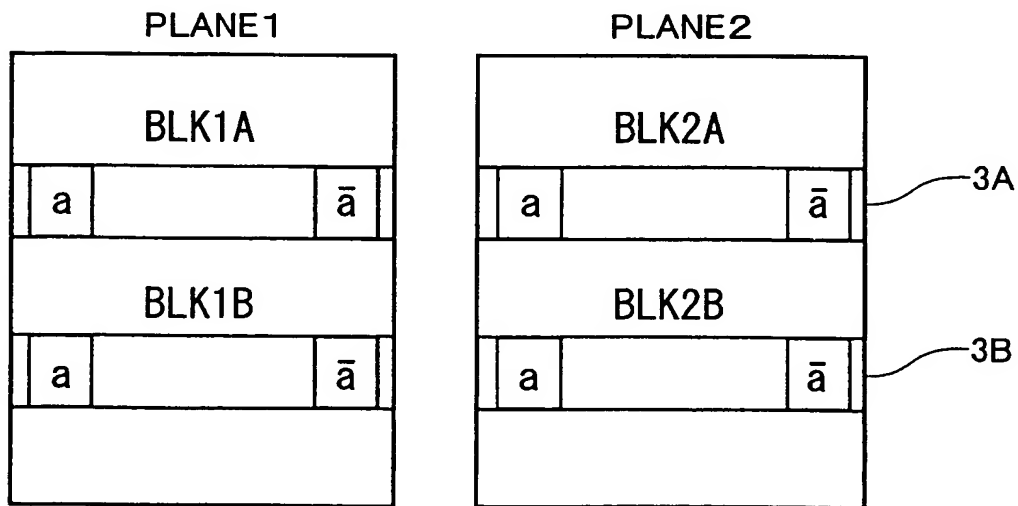


FIG.11

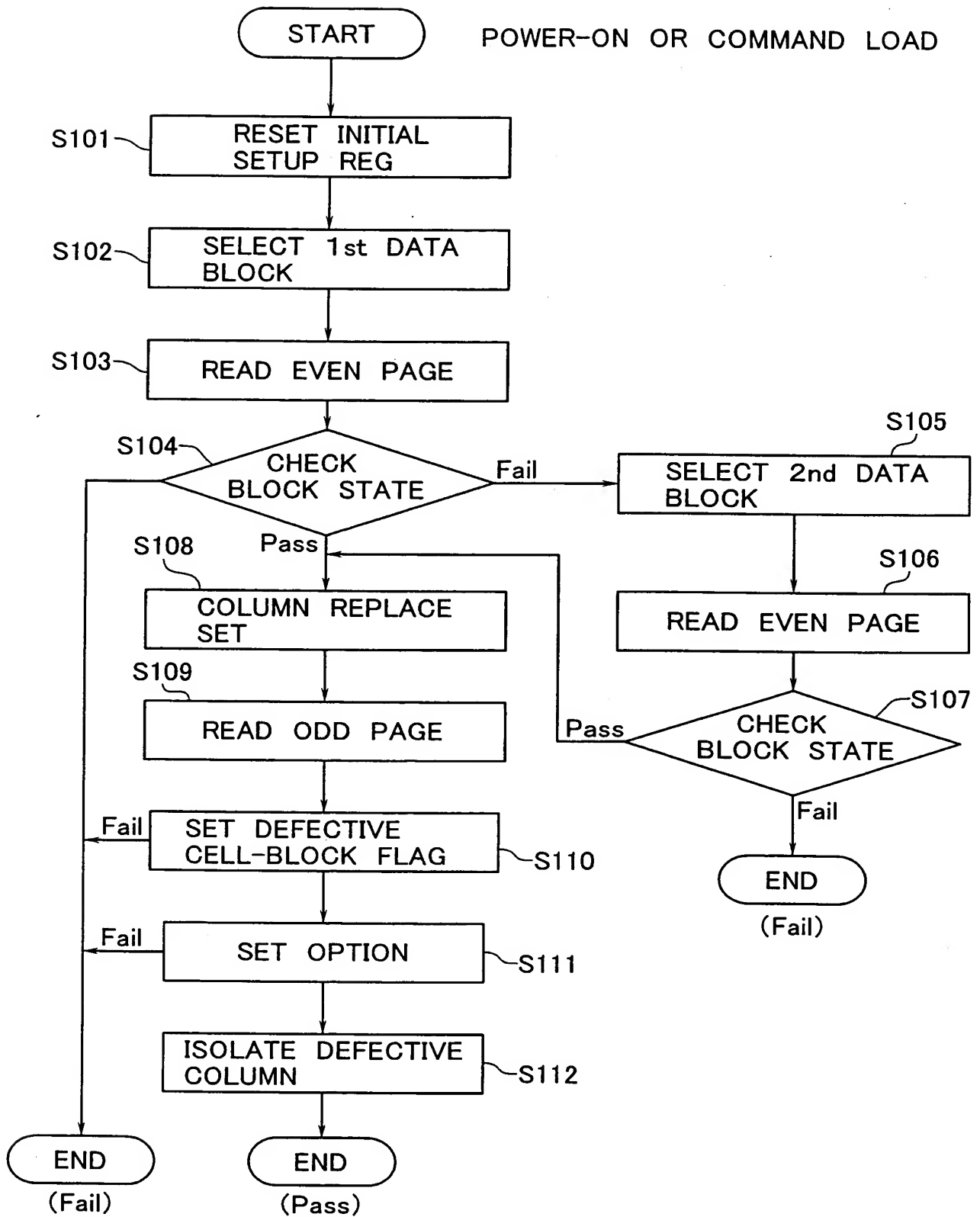


FIG.12

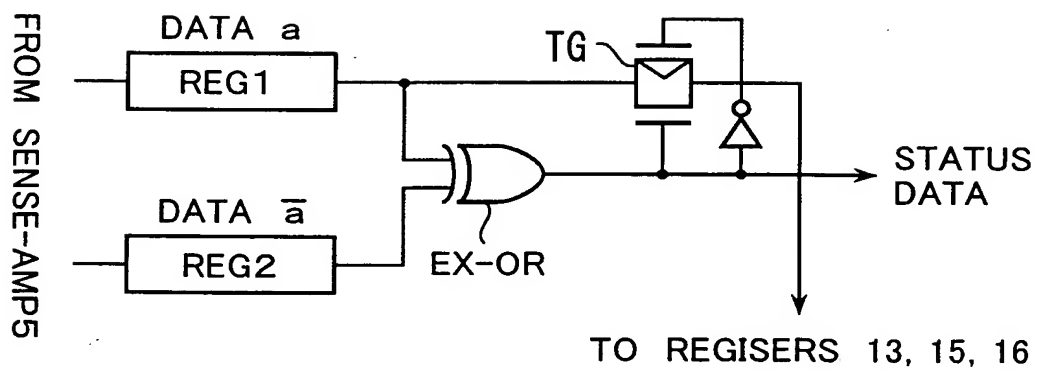


FIG.13

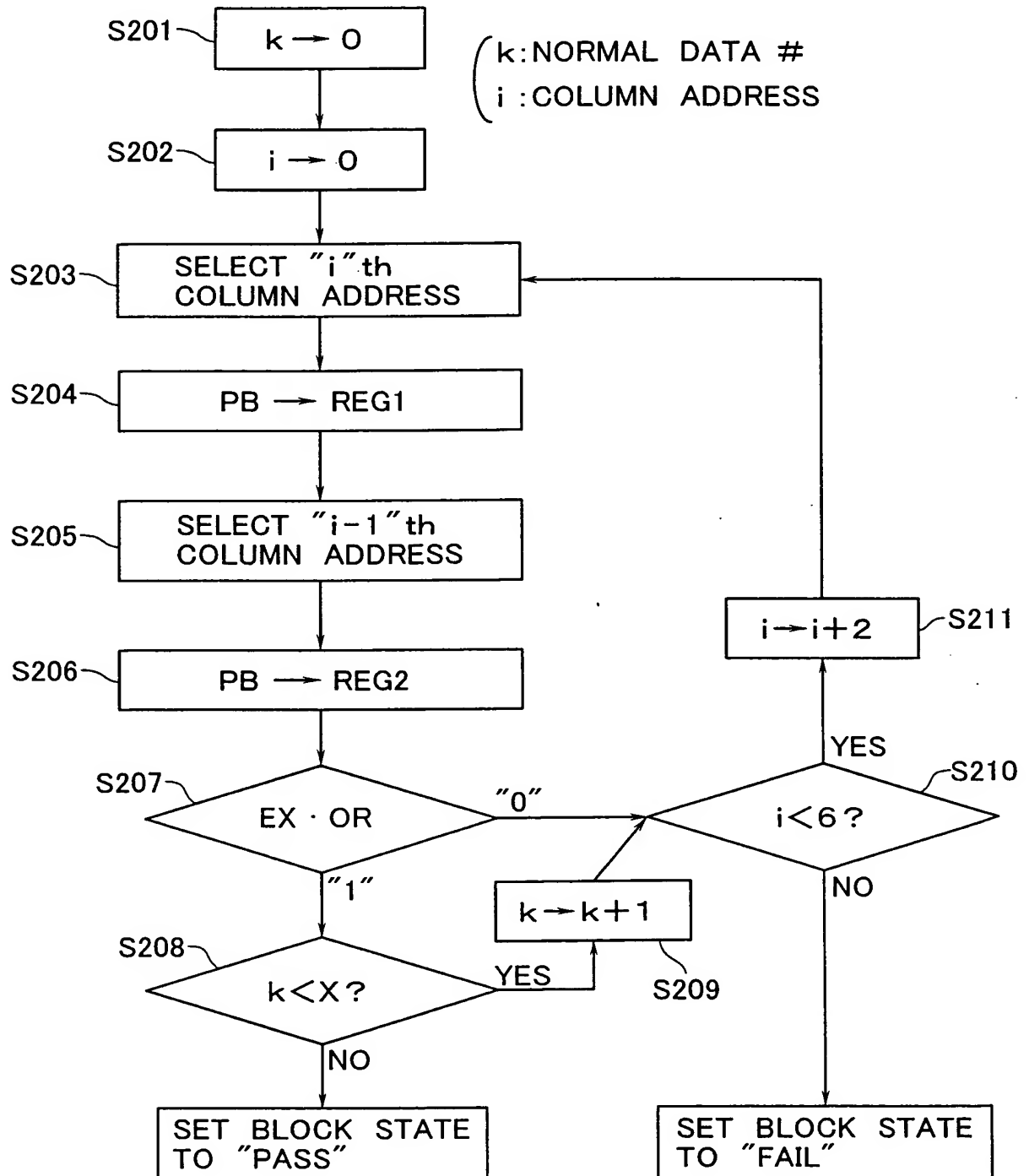
BLOCK STATE CHECH AT S104 & S107

FIG.14

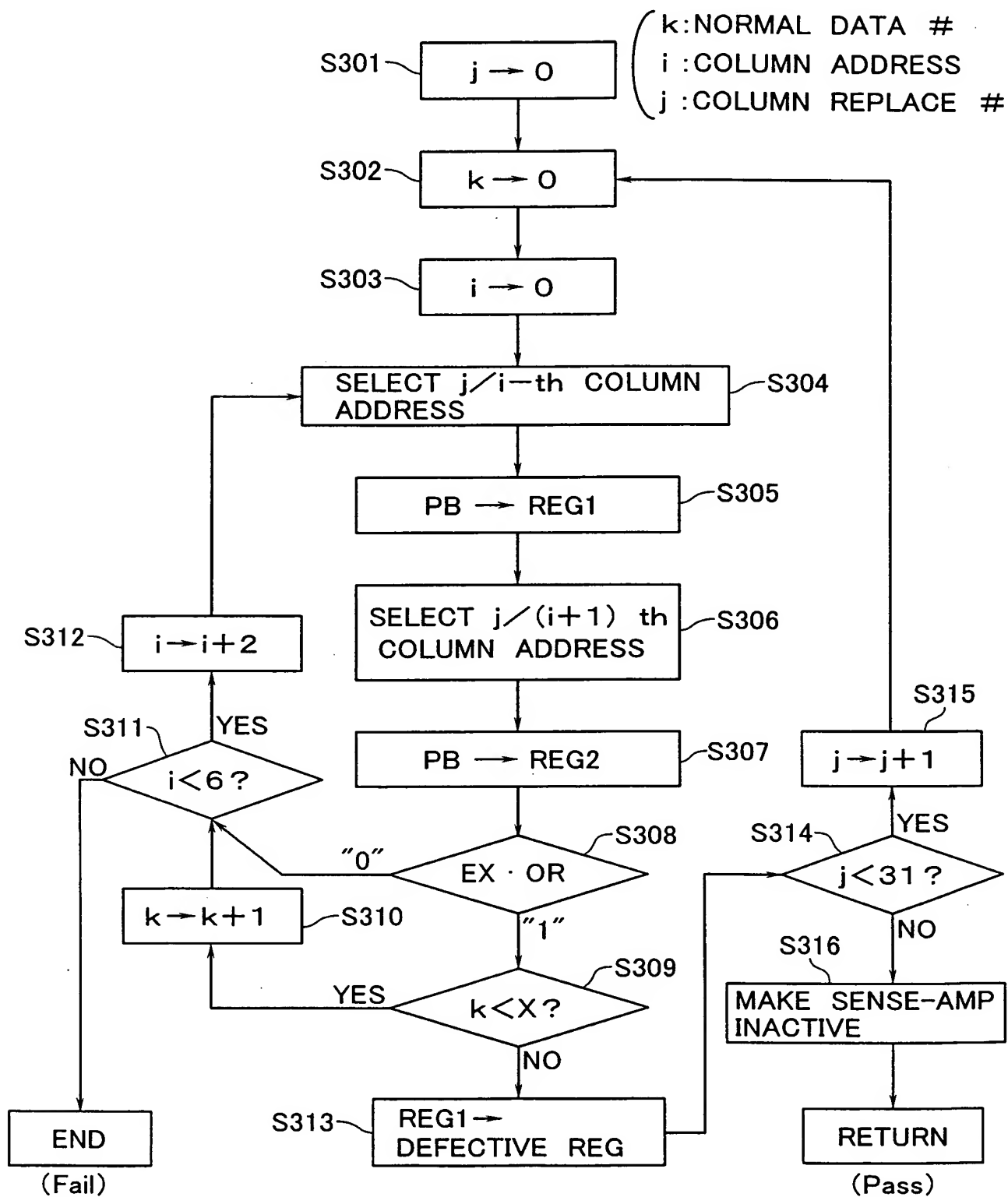
COLUMN REPLACE/SETTING AT S108

FIG.15

DEFECTIVE CELL-BLOCK  
FLAG SETUP AT S110  
OPTION SETUP AT S111

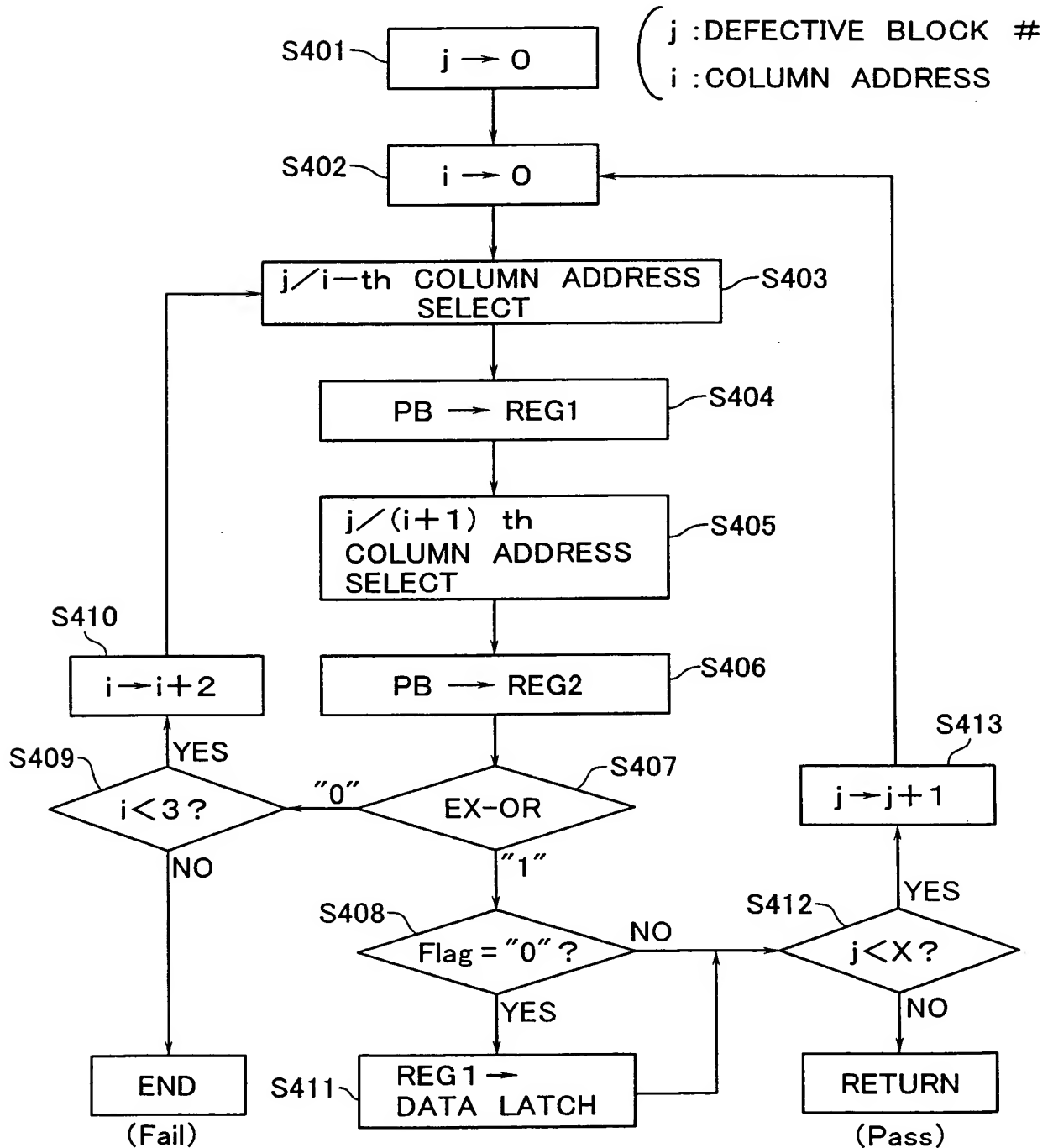


FIG.16

INITIAL SETUP DATA PROGRAMMING  
(WITHOUT AUTOMATIC TEST)

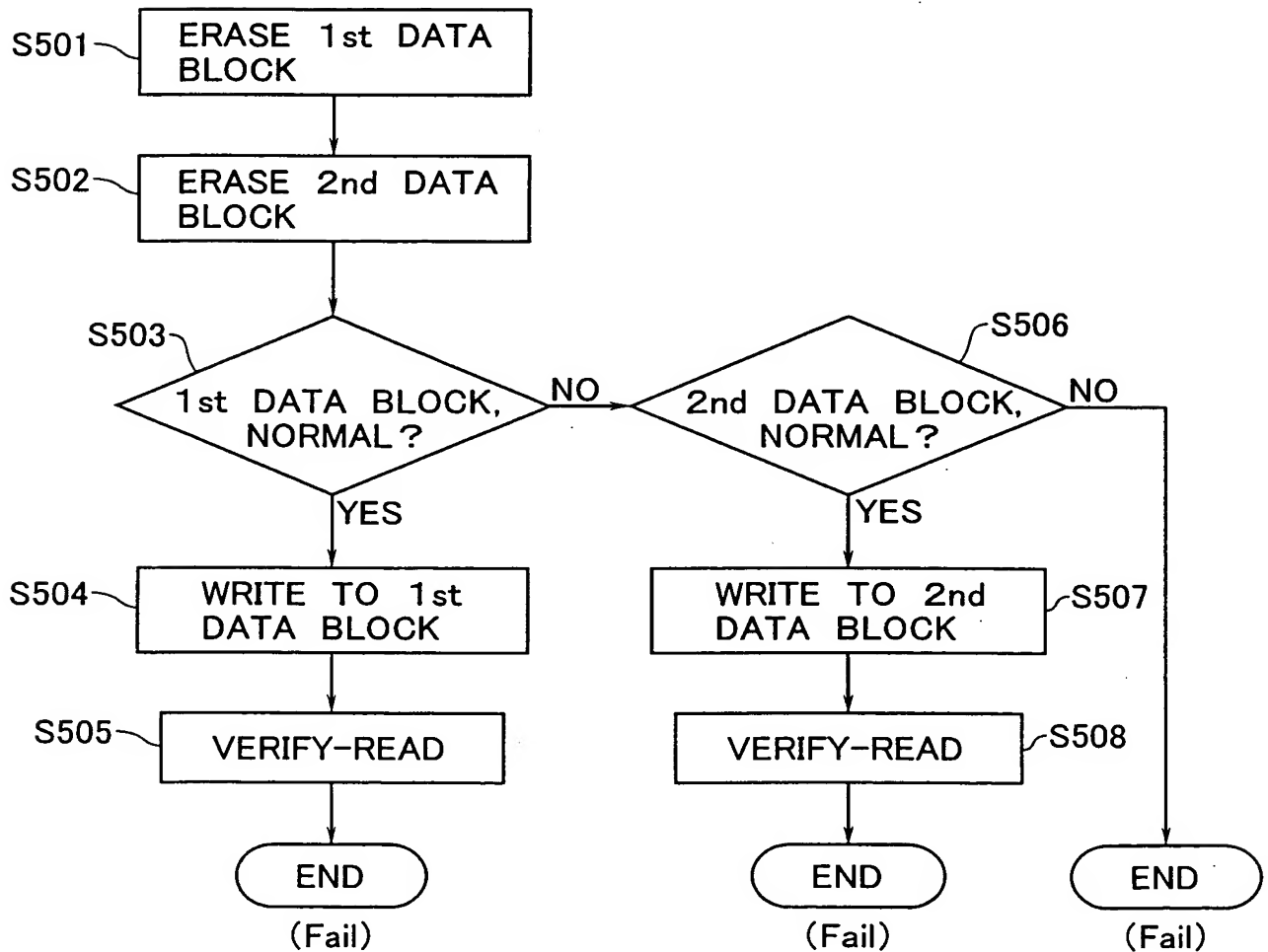


FIG.17

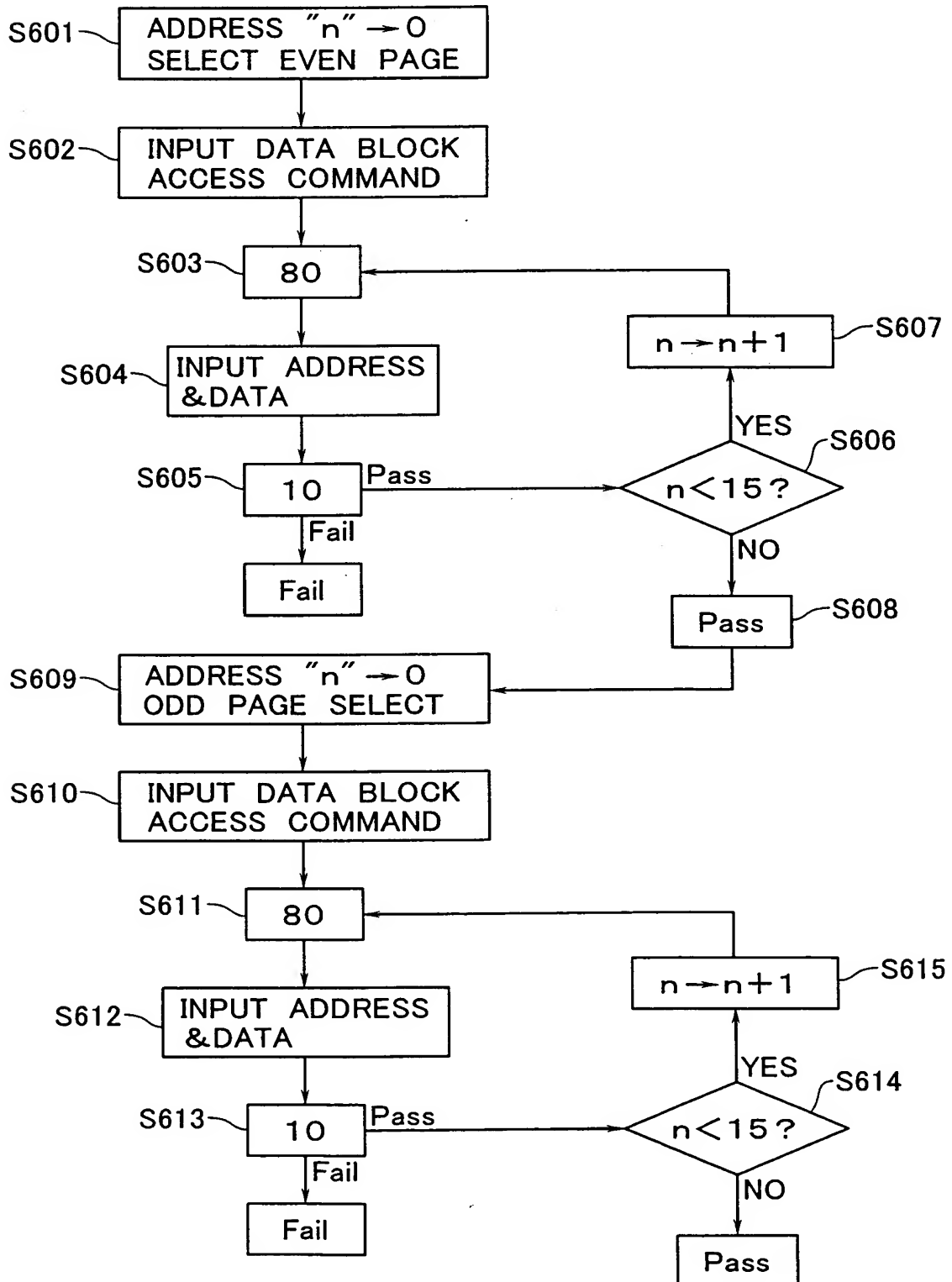
DATA BLOCK WRITE AT S504 & S507

FIG.18

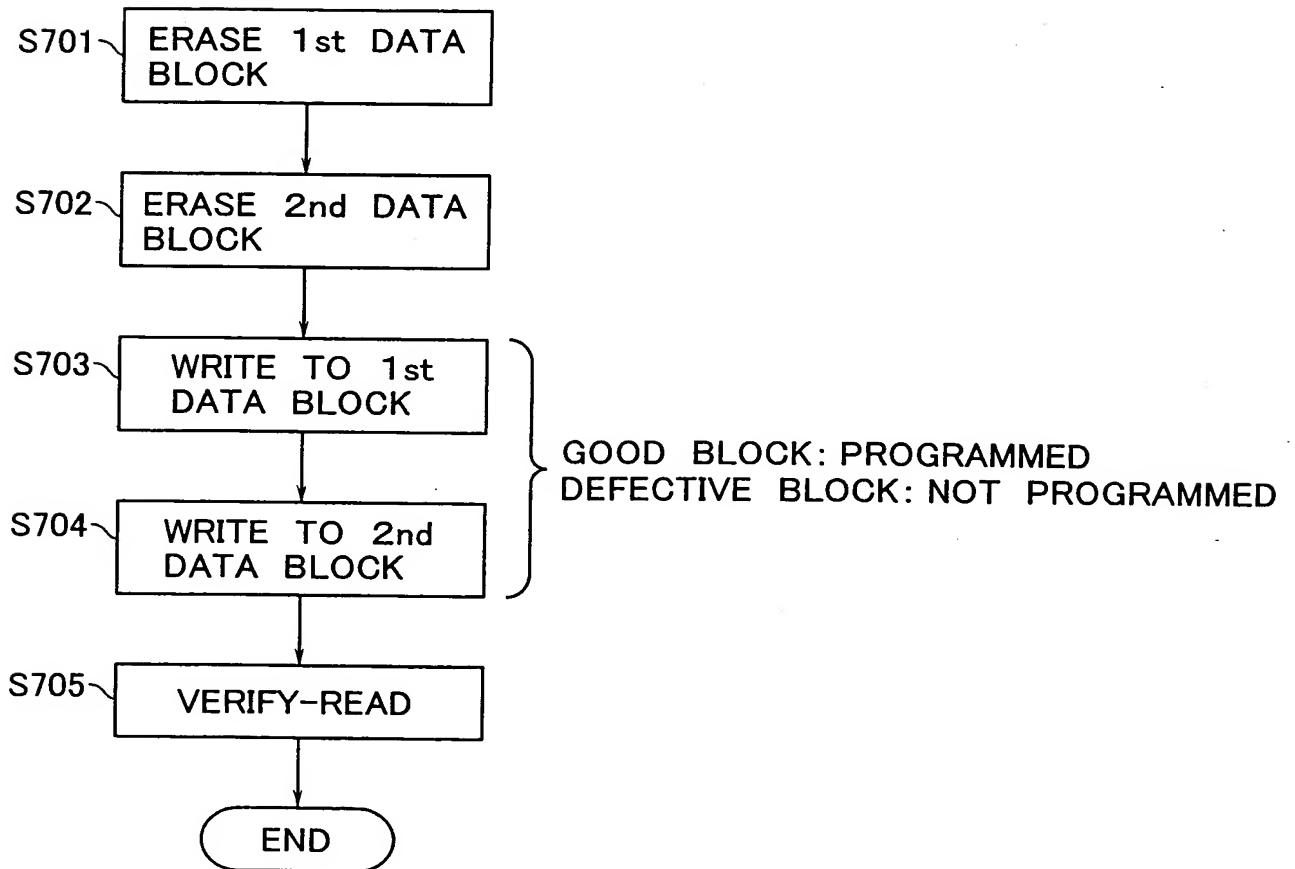
INITIAL SETUP DATA PROGRAMMING  
(WITH AUTOMATIC TEST)

FIG.19

DATA BLOCK WRITING S703 & S704